2SB0789, 2SB0789A (2SB789, 2SB789A)

Silicon PNP epitaxial planar type

For low-frequency driver amplification

■ Features

- ullet High collector-emitter voltage (Base open) V_{CEO}
- Large collector power dissipation P_C

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit		
Collector-base voltage	2SB0789	V _{CBO}	-100	V	
(Emitter open)	2SB0789A		-120		
Collector-emitter voltage	2SB0789	V _{CEO}	-100	V	
(Base open)	2SB0789A		-120		
Emitter-base voltage (Coll	V_{EBO}	-5	V		
Collector current	I_C	- 0.5	A		
Peak collector current	I _{CP}	-1	A		
Collector power dissipation	P _C	1	W		
Junction temperature	Tj	150	°C		
Storage temperature	T _{stg}	-55 to +150	°C		

Note) *: Print circuit board: Copper foil area of 1 cm² or more, and the board thickness of 1.7 mm for the collector portion.

Unit: mm 4.5±0.1 1.6±0.2 1.5±0.1 1.

Marking Symbol:

• 2SB0789: D

• 2SB0789A: E

■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage 2SB0789	V _{CEO}	$I_{\rm C} = -100 \mu A, I_{\rm B} = 0$	-100			V
(Base open) 2SB0789A		60/10°11'	-120			
Emitter-base voltage (Collector open)	V_{EBO}	$I_{\rm E} = -10 {\rm mA}, I_{\rm C} = 0$	-5			V
Forward current transfer ratio *1	h _{FE1} *2	$V_{CE} = -10 \text{ V}, I_{C} = -150 \text{ mA}$	90		220	_
	h _{FE2}	$V_{CE} = -5 \text{ V}, I_C = -500 \text{ mA}$	50			
Collector-emitter saturation voltage *1	V _{CE(sat)}	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$		- 0.2	- 0.6	V
Base-emitter saturation voltage *	V _{BE(sat)}	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$		- 0.85	-1.20	V
Transition frequency	f_T	$V_{CB} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		120		MHz
Collector output capacitance	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$			30	pF
(Common base, input open circuited)						

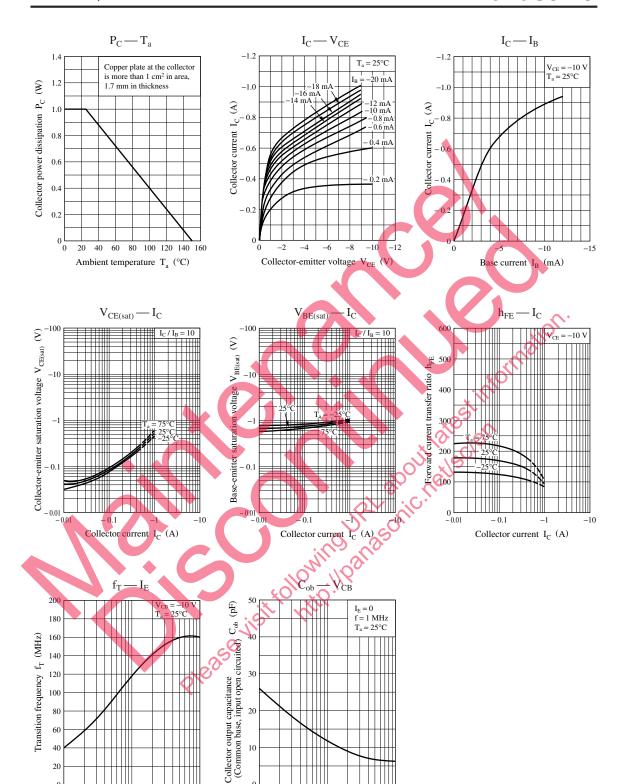
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Pulse measurement

*2: Rank classification

Rank	Q	R		
h _{FE1}	90 to 155	130 to 220		

Note) The part number in the parenthesis shows conventional part number.



100

10

Emitter current I_E (mA)

20

10

0 L

80

60 40

20

2

-10

Collector-base voltage V_{CB} (V)

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